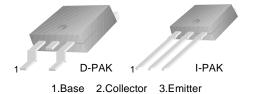


MJD210

D-PAK for Surface Mount Applications

- High DC Current Gain
- Low Collector Emitter Saturation Voltage
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PAK, " I " Suffix)



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	- 40	V
V _{CEO}	Collector-Emitter Voltage	- 25	V
V _{EBO}	Emitter-Base Voltage	- 8	V
I _C	Collector Current (DC)	- 5	Α
I _{CP}	Collector Peck Current (Pulse)	- 10	Α
I _B	Base Current	- 1	Α
P _C	Collector Dissipation (T _C = 25°C)	12.5	W
	Collector Dissipation (T _a = 25°C)	1.4	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V _{CEO} (sus)	* Collector-Emitter Sustaining Voltage	$I_C = -10 \text{mA}, I_B = 0$	-25		V
I _{CBO}	Collector Cut-off Current	$V_{CB} = -40V, I_{E} = 0$		-100	nA
I _{EBO}	Emitter Cut-off Current	$V_{EBO} = -8V, I_{C} = 0$		-100	nA
h _{FE}	* DC Current Gain	$V_{CE} = -1V, I_{C} = -500mA$	70		
		$V_{CE} = -1V, I_{C} = -2A$	45	180	
		$V_{CE} = -2V, I_{C} = -5A$	10		
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C = - 500mA, I _B = - 50mA		-0.3	V
		$I_C = -2A$, $I_B = -200mA$		-0.75	V
		I _C = -5A, I _B = -1A		-1.8	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C = - 5A, I _B = - 1A		-2.5	V
V _{BE} (on)	* Base-Emitter ON Voltage	V _{CE} = - 1V, I _C = - 2A		-1.6	V
f _T	Current Gain Bandwidth Product	V _{CE} = - 10V, I _C = - 100mA	65		MHz
C _{ob}	Output Capacitance	$V_{CB} = -10V, I_{E} = 0, f = 0.1MHz$		120	pF

* Pulse Test: PW≤300μs, Duty Cycle≤2%

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Typical Characteristics

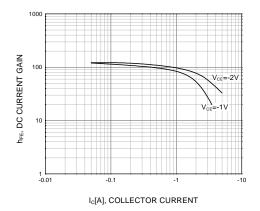


Figure 1. DC current Gain

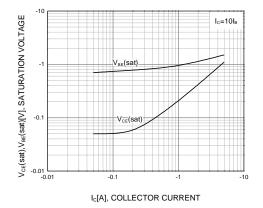


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

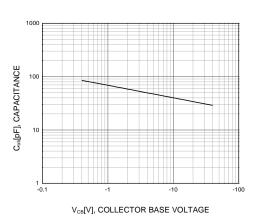


Figure 3. Collector Output Capacitance

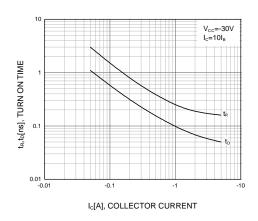


Figure 4. Turn On Time

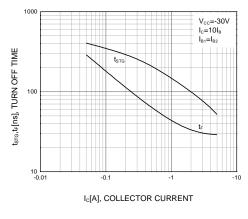


Figure 5. Turn Off Time

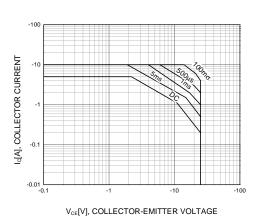


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

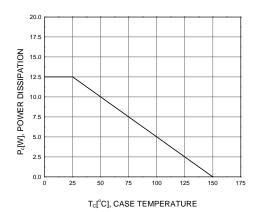
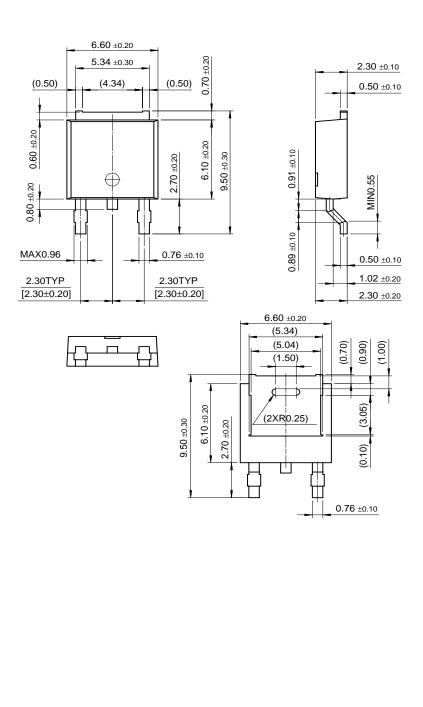


Figure 7. Power Derating

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Package Demensions

D-PAK



Dimensions in Millimeters

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